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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	168
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	208-LQFP
Supplier Device Package	208-LQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f429bet6

The over-drive mode allows operating at a higher frequency than the normal mode for a given voltage scaling.

– In Stop modes

The MR can be configured in two ways during stop mode:

MR operates in normal mode (default mode of MR in stop mode)

MR operates in under-drive mode (reduced leakage mode).

- LPR is used in the Stop modes:

  The LP regulator mode is configured by software when entering Stop mode.

  Like the MR mode, the LPR can be configured in two ways during stop mode:

  – LPR operates in normal mode (default mode when LPR is ON)

  – LPR operates in under-drive mode (reduced leakage mode).

- Power-down is used in Standby mode.

  The Power-down mode is activated only when entering in Standby mode. The regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption. The contents of the registers and SRAM are lost.

Refer to *Table 3* for a summary of voltage regulator modes versus device operating modes.

Two external ceramic capacitors should be connected on V_{CAP_1} and V_{CAP_2} pin. Refer to *Figure 22: Power supply scheme* and *Table 19: VCAP1/VCAP2 operating conditions*.

All packages have the regulator ON feature.

Table 3. Voltage regulator configuration mode versus device operating mode(1)

Voltage regulator configuration	Run mode	Sleep mode	Stop mode	Standby mode
Normal mode	MR	MR	MR or LPR	-
Over-drive mode(2)	MR	MR	-	-
Under-drive mode	-	-	MR or LPR	-
Power-down mode	-	-	-	Yes

1. '-' means that the corresponding configuration is not available.
2. The over-drive mode is not available when V_{DD} = 1.7 to 2.1 V.

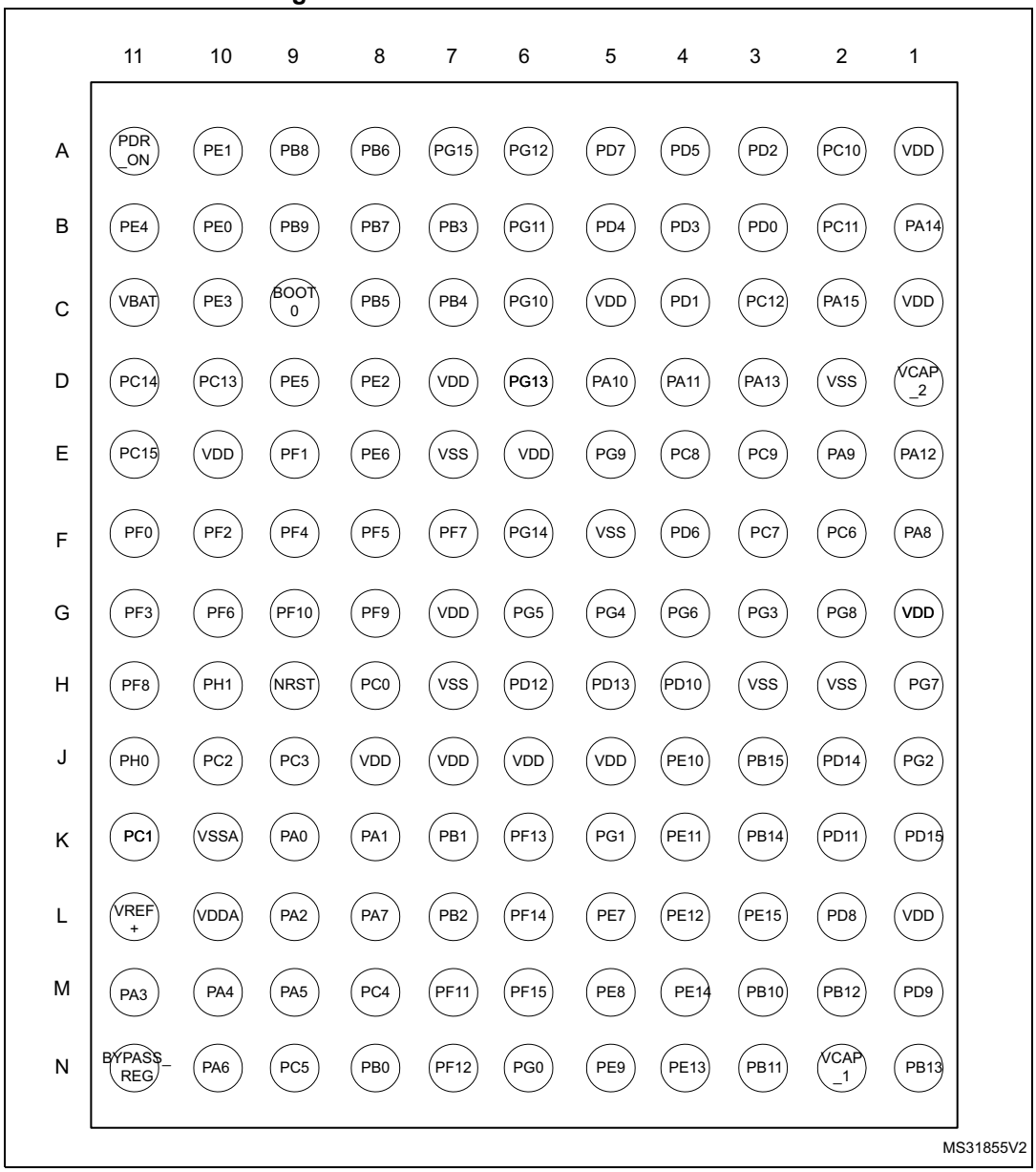
3.18.2 Regulator OFF

This feature is available only on packages featuring the BYPASS_REG pin. The regulator is disabled by holding BYPASS_REG high. The regulator OFF mode allows to supply externally a V_{12} voltage source through V_{CAP_1} and V_{CAP_2} pins.

Since the internal voltage scaling is not managed internally, the external voltage value must be aligned with the targeted maximum frequency. Refer to *Table 17: General operating conditions*.The two 2.2 µF ceramic capacitors should be replaced by two 100 nF decoupling capacitors. Refer to *Figure 22: Power supply scheme*.

When the regulator is OFF, there is no more internal monitoring on V_{12}. An external power supply supervisor should be used to monitor the V_{12} of the logic power domain. PA0 pin should be used for this purpose, and act as power-on reset on V_{12} power domain.

Figure 12. STM32F42x WLCSP143 ballout



1. The above figure shows the package bump view.

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number								Pin name (function after reset)(1)	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
58	80	H10	N14	99	K2	111	N10	PD11	I/O	FT	-	USART3_CTS, FMC_A16, EVENTOUT	-
59	81	J13	N13	100	H6	112	M10	PD12	I/O	FT	-	TIM4_CH1, USART3_RTS, FMC_A17, EVENTOUT	-
60	82	K12	M15	101	H5	113	M11	PD13	I/O	FT	-	TIM4_CH2, FMC_A18, EVENTOUT	-
-	83	-	-	102	-	114	J10	V_{SS}	S		-	-	-
-	84	F7	J13	103	L1	115	J11	V_{DD}	S		-	-	-
61	85	H11	M14	104	J2	116	L12	PD14	I/O	FT	-	TIM4_CH3, FMC_D0, EVENTOUT	-
62	86	J12	L14	105	K1	117	K13	PD15	I/O	FT	-	TIM4_CH4, FMC_D1, EVENTOUT	-
-	-	-	-	-	-	118	K12	PJ6	I/O	FT	-	LCD_R7, EVENTOUT	-
-	-	-	-	-	-	119	J12	PJ7	I/O	FT	-	LCD_G0, EVENTOUT	-
-	-	-	-	-	-	120	H12	PJ8	I/O	FT	-	LCD_G1, EVENTOUT	-
-	-	-	-	-	-	121	J13	PJ9	I/O	FT	-	LCD_G2, EVENTOUT	-
-	-	-	-	-	-	122	H13	PJ10	I/O	FT	-	LCD_G3, EVENTOUT	-
-	-	-	-	-	-	123	G12	PJ11	I/O	FT	-	LCD_G4, EVENTOUT	-
-	-	-	-	-	-	124	H11	VDD	I/O	FT	-	-	-
-	-	-	-	-	-	125	H10	VSS	I/O	FT	-	-	-
-	-	-	-	-	-	126	G13	PK0	I/O	FT	-	LCD_G5, EVENTOUT	-
-	-	-	-	-	-	127	F12	PK1	I/O	FT	-	LCD_G6, EVENTOUT	-
-	-	-	-	-	-	128	F13	PK2	I/O	FT	-	LCD_G7, EVENTOUT	-
-	87	H13	L15	106	J1	129	M13	PG2	I/O	FT	-	FMC_A12, EVENTOUT	-
-	88	NC (2)	K15	107	G3	130	M12	PG3	I/O	FT	-	FMC_A13, EVENTOUT	-
-	89	H12	K14	108	G5	131	N12	PG4	I/O	FT	-	FMC_A14/FMC_BA0, EVENTOUT	-
-	90	G13	K13	109	G6	132	N11	PG5	I/O	FT	-	FMC_A15/FMC_BA1, EVENTOUT	-

Table 10. STM32F427xx and STM32F429xx pin and ball definitions (continued)

Pin number								Pin name (function after reset)[1]	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP100	LQFP144	UFBGA169	UFBGA176	LQFP176	WLCSP143	LQFP208	TFBGA216						
-	91	G11	J15	110	G4	133	J15	PG6	I/O	FT	-	FMC_INT2, DCMI_D12, LCD_R7, EVENTOUT	-
-	92	G12	J14	111	H1	134	J14	PG7	I/O	FT	-	USART6_CK, FMC_INT3, DCMI_D13, LCD_CLK, EVENTOUT	-
-	93	F13	H14	112	G2	135	H14	PG8	I/O	FT	-	SPI6_NSS, USART6_RTS, ETH_PPS_OUT, FMC_SDCLK, EVENTOUT	-
-	94	J7	G12	113	D2	136	G10	V_{SS}	S		-	-	-
-	95	E6	H13	114	G1	137	G11	V_{DD}	S		-	-	-
63	96	F9	H15	115	F2	138	H15	PC6	I/O	FT	-	TIM3_CH1, TIM8_CH1, I2S2_MCK, USART6_TX, SDIO_D6, DCMI_D0, LCD_HSYNC, EVENTOUT	-
64	97	F10	G15	116	F3	139	G15	PC7	I/O	FT	-	TIM3_CH2, TIM8_CH2, I2S3_MCK, USART6_RX, SDIO_D7, DCMI_D1, LCD_G6, EVENTOUT	-
65	98	F11	G14	117	E4	140	G14	PC8	I/O	FT	-	TIM3_CH3, TIM8_CH3, USART6_CK, SDIO_D0, DCMI_D2, EVENTOUT	-
66	99	F12	F14	118	E3	141	F14	PC9	I/O	FT	-	MCO2, TIM3_CH4, TIM8_CH4, I2C3_SDA, I2S_CKIN, SDIO_D1, DCMI_D3, EVENTOUT	-
67	100	E13	F15	119	F1	142	F15	PA8	I/O	FT	-	MCO1, TIM1_CH1, I2C3_SCL, USART1_CK, OTG_FS_SOF, LCD_R6, EVENTOUT	-

Table 12. STM32F427xx and STM32F429xx alternate function mapping

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/2/3/4/5/6	SPI2/3/SAI1	SPI3/USART1/2/3	USART6/UART4/5/7/8	CAN1/2/TIM12/13/14/LCD	OTG2_HS/OTG1_FS	ETH	FMC/SDIO/OTG2_FS	DCMI	LCD	SYS
Port A	PA0	-	TIM2_CH1/TIM2_ETR	TIM5_CH1	TIM8_ETR	-	-	-	USART2_CTS	UART4_TX	-	-	ETH_MII_CRS	-	-	-	EVENTOUT
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-	-	USART2_RTS	UART4_RX	-	-	ETH_MII_RX_CLK/ETH_RMII_REF_CLK	-	-	-	EVENTOUT
	PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-	-	USART2_TX	-	-	-	ETH_MDIO	-	-	-	EVENTOUT
	PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-	-	-	USART2_RX	-	-	OTG_HS_ULPI_D0	ETH_MII_COL	-	-	LCD_B5	EVENTOUT
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS/I2S3_WS	USART2_CK	-	-	-	-	OTG_HS_SOF	DCMI_HSYNC	LCD_VSYNC	EVENTOUT
	PA5	-	TIM2_CH1/TIM2_ETR	-	TIM8_CH1N	-	SPI1_SCK	-	-	-	-	OTG_HS_ULPI_CK	-	-	-	-	EVENTOUT
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	-	SPI1_MISO	-	-	-	TIM13_CH1	-	-	-	DCMI_PIXCLK	LCD_G2	EVENTOUT
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	-	SPI1_MOSI	-	-	-	TIM14_CH1	-	ETH_MII_RX_DV/ETH_RMII_CRS_DV	-	-	-	EVENTOUT
	PA8	MCO1	TIM1_CH1	-	-	I2C3_SCL	-	-	USART1_CK	-	-	OTG_FS_SOF	-	-	-	LCD_R6	EVENTOUT
	PA9	-	TIM1_CH2	-	-	I2C3_SMBA	-	-	USART1_TX	-	-	-	-	-	DCMI_D0	-	EVENTOUT
	PA10	-	TIM1_CH3	-	-	-	-	-	USART1_RX	-	-	OTG_FS_ID	-	-	DCMI_D1	-	EVENTOUT
	PA11	-	TIM1_CH4	-	-	-	-	-	USART1_CTS	-	CAN1_RX	OTG_FS_DM	-	-	-	LCD_R4	EVENTOUT
	PA12	-	TIM1_ETR	-	-	-	-	-	USART1_RTS	-	CAN1_TX	OTG_FS_DP	-	-	-	LCD_R5	EVENTOUT

Table 12. STM32F427xx and STM32F429xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/2/3/4/5/6	SPI2/3/SAI1	SPI3/USART1/2/3	USART6/UART4/5/7/8	CAN1/2/TIM12/13/14/LCD	OTG2_HS/OTG1_FS	ETH	FMC/SDIO/OTG2_FS	DCMI	LCD	SYS
Port H	PH7	-	-	-	-	I2C3_SCL	SPI5_MISO	-	-	-	-	-	ETH_MII_RXD3	FMC_SDCKE1	DCMI_D9	-	-
	PH8	-	-	-	-	I2C3_SDA	-	-	-	-	-	-	-	FMC_D16	DCMI_HSYNC	LCD_R2	EVENTOUT
	PH9	-	-	-	-	I2C3_SMBA	-	-	-	-	TIM12_CH2	-	-	FMC_D17	DCMI_D0	LCD_R3	EVENTOUT
	PH10	-	-	TIM5_CH1	-	-	-	-	-	-	-	-	-	FMC_D18	DCMI_D1	LCD_R4	EVENTOUT
	PH11	-	-	TIM5_CH2	-	-	-	-	-	-	-	-	-	FMC_D19	DCMI_D2	LCD_R5	EVENTOUT
	PH12	-	-	TIM5_CH3	-	-	-	-	-	-	-	-	-	FMC_D20	DCMI_D3	LCD_R6	EVENTOUT
	PH13	-	-	-	TIM8_CH1N	-	-	-	-	-	CAN1_TX	-	-	FMC_D21	-	LCD_G2	EVENTOUT
	PH14	-	-	-	TIM8_CH2N	-	-	-	-	-	-	-	-	FMC_D22	DCMI_D4	LCD_G3	EVENTOUT
	PH15	-	-	-	TIM8_CH3N	-	-	-	-	-	-	-	-	FMC_D23	DCMI_D11	LCD_G4	EVENTOUT
Port I	PI0	-	-	TIM5_CH4	-	-	SPI2_NSS/I2S2_WS	-	-	-	-	-	-	FMC_D24	DCMI_D13	LCD_G5	EVENTOUT
	PI1	-	-	-	-	-	SPI2_SCK/I2S2_CK	-	-	-	-	-	-	FMC_D25	DCMI_D8	LCD_G6	EVENTOUT
	PI2	-	-	-	TIM8_CH4	-	SPI2_MISO	I2S2ext_SD	-	-	-	-	-	FMC_D26	DCMI_D9	LCD_G7	EVENTOUT
	PI3	-	-	-	TIM8_ETR	-	SPI2_MOSI/I2S2_SD							FMC_D27	DCMI_D10		EVENTOUT
	PI4	-	-	-	TIM8_BKIN	-	-	-	-	-	-	-	-	FMC_NBL2	DCMI_D5	LCD_B4	EVENTOUT
	PI5	-	-	-	TIM8_CH1	-	-	-	-	-	-	-	-	FMC_NBL3	DCMI_VSYNC	LCD_B5	EVENTOUT
	PI6	-	-	-	TIM8_CH2	-	-	-	-	-	-	-	-	FMC_D28	DCMI_D6	LCD_B6	EVENTOUT

Table 25. Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)			Unit
					TA= 25 °C	TA=85 °C	TA=105 °C	
I_{DD}	Supply current in RUN mode	All Peripherals enabled(2)(3)	180	103	112	140	151	mA
			168	98	107	126	144	
			150	87	95	112	128	
			144	85	92	108	124	
			120	66	71	85	99	
			90	54	58	69	80	
			60	37	39	47	55	
			30	20	24	39	51	
			25	17	21	35	48	
			16	12	16	30	42	
			8	7	11	24	37	
			4	5	8	22	35	
			2	3	7	21	34	
		All Peripherals disabled(3)	180	57	62	87	106	
			168	50	54	76	93	
			150	46	50	70	86	
			144	45	49	68	84	
			120	36	41	56	69	
			90	29	34	46	57	
			60	21	24	33	41	
			30	13	17	31	44	
			25	11	15	28	41	
			16	8	12	25	38	
			8	5	9	23	35	
			4	4	7	21	34	
			2	3	6.5	20	33	

1. Guaranteed by characterization unless otherwise specified.
2. When analog peripheral blocks such as ADCs, DACs, HSE, LSE, HSI, or LSI are ON, an additional power consumption should be considered.
3. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA per ADC for the analog part.

Table 32. Typical current consumption in Sleep mode, regulator ON, V_{DD}=1.7 V(1)

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Unit
I_{DD}	Supply current in Sleep mode from V_{DD} supply	All Peripherals enabled	168	65.5	mA
			150	55.5	
			144	53.5	
			120	39.0	
			90	31.6	
			60	21.7	
			30	9.8	
			25	8.8	
		All Peripherals disabled	168	15.7	
			150	13.7	
			144	12.7	
			120	9.7	
			90	7.7	
			60	5.7	
			30	4.7	
			25	2.8	

1. When peripherals are enabled, the power consumption corresponding to the analog part of the peripherals (such as ADC, or DAC) is not included.

On-chip peripheral current consumption

The MCU is placed under the following conditions:

- At startup, all I/O pins are in analog input configuration.
- All peripherals are disabled unless otherwise mentioned.
- I/O compensation cell enabled.
- The ART accelerator is ON.
- Scale 1 mode selected, internal digital voltage V12 = 1.32 V.
- HCLK is the system clock. $f_{PCLK1} = f_{HCLK}/4$, and $f_{PCLK2} = f_{HCLK}/2$.
  The given value is calculated by measuring the difference of current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on
  - f_{HCLK} = 180 MHz (Scale1 + over-drive ON), f_{HCLK} = 144 MHz (Scale 2), f_{HCLK} = 120 MHz (Scale 3)"
- Ambient operating temperature is 25 °C and V_{DD}=3.3 V.

Table 35. Peripheral current consumption

Peripheral		I_{DD}(Typ)(1)			Unit
		Scale 1	Scale 2	Scale 3	
AHB1 (up to 180 MHz)	GPIOA	2.50	2.36	2.08	µA/MHz
	GPIOB	2.56	2.36	2.08	
	GPIOC	2.44	2.29	2.00	
	GPIOD	2.50	2.36	2.08	
	GPIOE	2.44	2.29	2.00	
	GPIOF	2.44	2.29	2.00	
	GPIOG	2.39	2.22	2.00	
	GPIOH	2.33	2.15	1.92	
	GPIOI	2.39	2.22	2.00	
	GPIOJ	2.33	2.15	1.92	
	GPIOK	2.33	2.15	1.92	
	OTG_HS+ULPI	27.00	24.86	21.92	
	CRC	0.44	0.42	0.33	
	BKPSRAM	0.78	0.69	0.58	
	DMA1	25.33	23.26	20.50	
	DMA2	24.72	22.71	20.00	
	DMA2D	28.50	26.32	23.33	
	ETH_MAC ETH_MAC_TX ETH_MAC_RX ETH_MAC_PTP	21.56	20.07	17.75	

Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard I/O. The external clock signal has to respect the *Table 56: I/O static characteristics*. However, the recommended clock input waveform is shown in *Figure 28*.

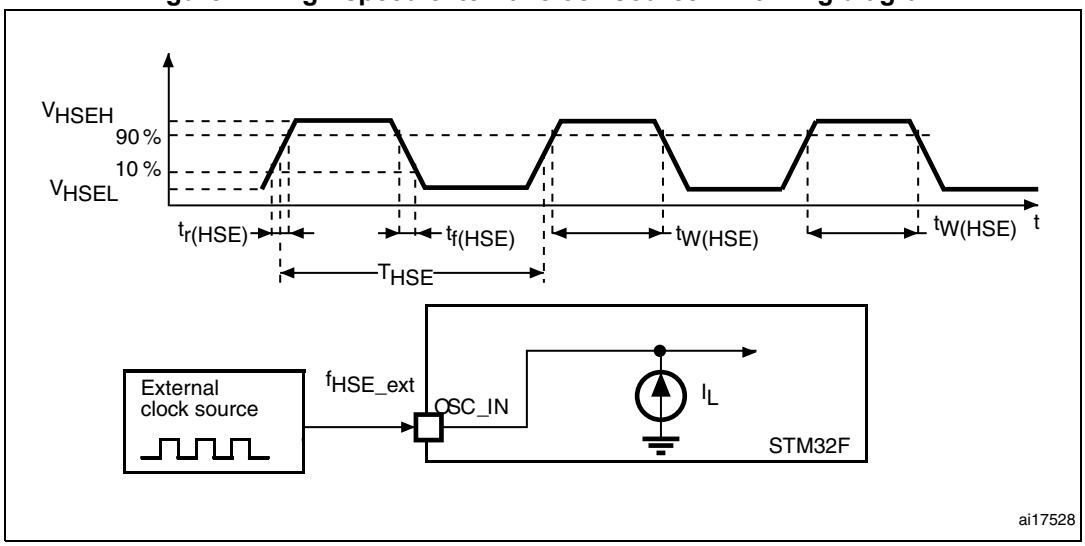
The characteristics given in *Table 38* result from tests performed using an low-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 17*.

Table 38. Low-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User External clock source frequency(1)		-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSE)}$ $t_{f(LSE)}$	OSC32_IN high or low time(1)		450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time(1)		-	-	50	
$C_{in(LSE)}$	OSC32_IN input capacitance(1)		-	5	-	pF
$DuCy_{(LSE)}$	Duty cycle		30	-	70	%
I_L	OSC32_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design.

Figure 27. High-speed external clock source AC timing diagram



Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application, executing EEMBC? code, is running. This emission test is compliant with SAE IEC61967-2 standard which specifies the test board and the pin loading.

Table 52. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{CPU}]	Max vs. [f_{HSE}/f_{CPU}]	Unit
				25/168 MHz	25/180 MHz	
S_{EMI}	Peak level	V_{DD} = 3.3 V, T_A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, ART ON, all peripheral clocks enabled, clock dithering disabled.	0.1 to 30 MHz	16	19	dBµV
			30 to 130 MHz	23	23	
			130 MHz to 1GHz	25	22	
			SAE EMI Level	4	4	-
		V_{DD} = 3.3 V, T_A = 25 °C, LQFP176 package, conforming to SAE J1752/3 EEMBC, ART ON, all peripheral clocks enabled, clock dithering enabled	0.1 to 30 MHz	17	16	dBµV
			30 to 130 MHz	8	10	
			130 MHz to 1GHz	11	16	
			SAE EMI level	3.5	3.5	-

Figure 49. Ethernet MII timing diagram

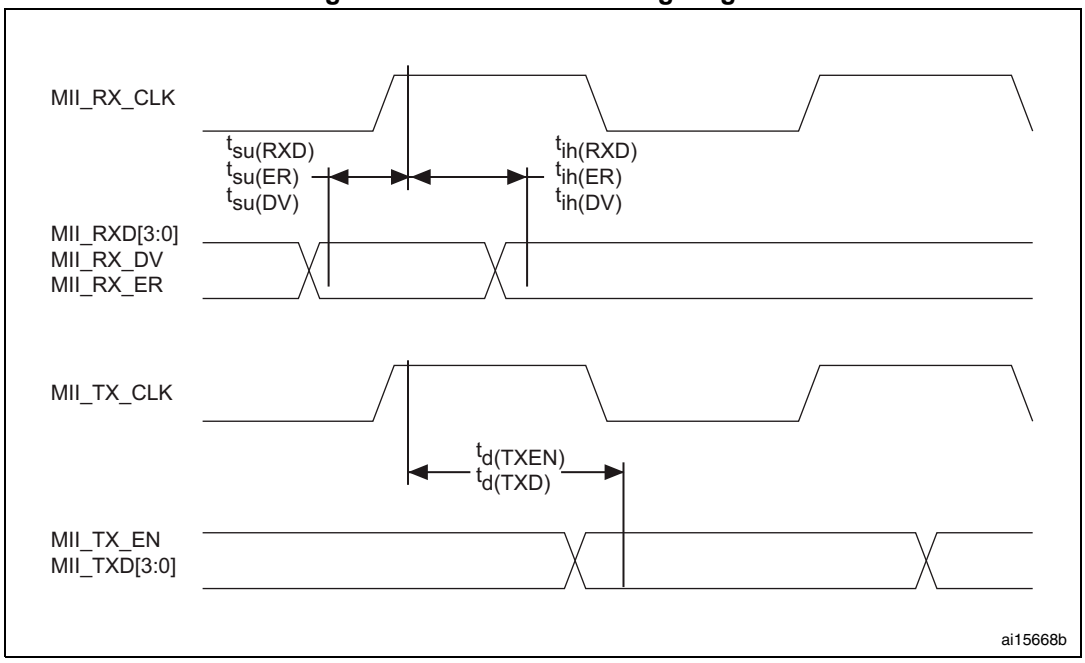


Table 73. Dynamics characteristics: Ethernet MAC signals for MII(1)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{su(RXD)}$	Receive data setup time	1.71 V < V_{DD} < 3.6 V	9	-	-	ns
$t_{ih(RXD)}$	Receive data hold time		10	-	-	
$t_{su(DV)}$	Data valid setup time		9	-	-	
$t_{ih(DV)}$	Data valid hold time		8	-	-	
$t_{su(ER)}$	Error setup time		6	-	-	
$t_{ih(ER)}$	Error hold time		8	-	-	
$t_{d(TXEN)}$	Transmit enable valid delay time	2.7 V < V_{DD} < 3.6 V	8	10	14	
		1.71 V < V_{DD} < 3.6 V	8	10	16	
$t_{d(TXD)}$	Transmit data valid delay time	2.7 V < V_{DD} < 3.6 V	7.5	10	15	
		1.71 V < V_{DD} < 3.6 V	7.5	10	17	

1. Guaranteed by characterization results.

CAN (controller area network) interface

Refer to *Section 6.3.17: I/O port characteristics* for more details on the input/output alternate function characteristics (CANx_TX and CANx_RX).

6.3.26 FMC characteristics

Unless otherwise specified, the parameters given in *Table 86* to *Table 101* for the FMC interface are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage conditions summarized in *Table 17*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10 except at V_{DD} range 1.7 to 2.1V where OSPEEDRy[1:0] = 11
- Measurement points are done at CMOS levels: $0.5V_{DD}$

Refer to *Section 6.3.17: I/O port characteristics* for more details on the input/output characteristics.

Asynchronous waveforms and timings

Figure 55 through *Figure 58* represent asynchronous waveforms and *Table 86* through *Table 93* provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- AddressSetupTime = 0x1
- AddressHoldTime = 0x1
- DataSetupTime = 0x1 (except for asynchronous NWAIT mode , DataSetupTime = 0x5)
- BusTurnAroundDuration = 0x0
- For SDRAM memories, V_{DD} ranges from 2.7 to 3.6 V and maximum frequency FMC_SDCLK = 90 MHz
- For Mobile LPSDR SDRAM memories, V_{DD} ranges from 1.7 to 1.95 V and maximum frequency FMC_SDCLK = 84 MHz

Table 86. Asynchronous non-multiplexed SRAM/PSRAM/NOR - read timings(1)(2) (continued)

Symbol	Parameter	Min	Max	Unit
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	ns
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	ns
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	-	0	ns
$t_{w(NADV)}$	FMC_NADV low time	-	T_{HCLK} +1	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Table 87. Asynchronous non-multiplexed SRAM/PSRAM/NOR read - NWAIT timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$7T_{HCLK}$+0.5	$7T_{HCLK}$+1	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK}$ − 1.5	$5T_{HCLK}$ +2	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK}$+1.5	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}$+1	-	

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Table 90. Asynchronous multiplexed PSRAM/NOR read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK} - 1$	$3T_{HCLK}+0.5$	ns
$t_{v(NOE\_NE)}$	FMC_NEx low to FMC_NOE low	$2T_{HCLK} - 0.5$	$2T_{HCLK}$	ns
$t_{tw(NOE)}$	FMC_NOE low time	$T_{HCLK} - 1$	$T_{HCLK}+1$	ns
$t_{h(NE\_NOE)}$	FMC_NOE high to FMC_NE high hold time	1	-	ns
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	2	ns
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0	2	ns
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK} - 0.5$	$T_{HCLK}+0.5$	ns
$t_{h(AD\_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high)	0	-	ns
$t_{h(A\_NOE)}$	Address hold time after FMC_NOE high	$T_{HCLK} - 0.5$	-	ns
$t_{h(BL\_NOE)}$	FMC_BL time after FMC_NOE high	0	-	ns
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	2	ns
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK}+1.5$	-	ns
$t_{su(Data\_NOE)}$	Data to FMC_NOE high setup time	$T_{HCLK}+1$	-	ns
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	ns
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Table 91. Asynchronous multiplexed PSRAM/NOR read-NWAIT timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}+0.5$	$8T_{HCLK}+2$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK} - 1$	$5T_{HCLK}+1.5$	ns
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK}+1.5$	-	ns
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+1$		ns

1. C_L = 30 pF.
2. Guaranteed by characterization results.

Table 102. SDRAM read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK} - 0.5$	$2T_{HCLK}+0.5$	ns
$t_{su(SDCLKH\_Data)}$	Data input setup time	2	-	
$t_{h(SDCLKH\_Data)}$	Data input hold time	0	-	
$t_{d(SDCLKL\_Add)}$	Address valid time	-	1.5	
$t_{d(SDCLKL-SDNE)}$	Chip select valid time	-	0.5	
$t_{h(SDCLKL\_SDNE)}$	Chip select hold time	0	-	
$t_{d(SDCLKL\_SDNRAS)}$	SDNRAS valid time	-	0.5	
$t_{h(SDCLKL\_SDNRAS)}$	SDNRAS hold time	0	-	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS valid time	-	0.5	
$t_{h(SDCLKL\_SDNCAS)}$	SDNCAS hold time	0	-	

1. CL = 30 pF on data and address lines. CL=15pF on FMC_SDCLK.
2. Guaranteed by characterization results.

Table 103. LPSDR SDRAM read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{W(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK} - 0.5$	$2T_{HCLK}+0.5$	ns
$t_{su(SDCLKH\_Data)}$	Data input setup time	2.5	-	
$t_{h(SDCLKH\_Data)}$	Data input hold time	0	-	
$t_{d(SDCLKL\_Add)}$	Address valid time	-	1	
$t_{d(SDCLKL\_SDNE)}$	Chip select valid time	-	1	
$t_{h(SDCLKL\_SDNE)}$	Chip select hold time	1	-	
$t_{d(SDCLKL\_SDNRAS}$	SDNRAS valid time	-	1	
$t_{h(SDCLKL\_SDNRAS)}$	SDNRAS hold time	1	-	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS valid time	-	1	
$t_{h(SDCLKL\_SDNCAS)}$	SDNCAS hold time	1	-	

1. CL = 10 pF.
2. Guaranteed by characterization results.

Table 104. SDRAM write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK} - 0.5$	$2T_{HCLK}+0.5$	ns
$t_{d(SDCLKL\_Data)}$	Data output valid time	-	3.5	
$t_{h(SDCLKL\_Data)}$	Data output hold time	0	-	
$t_{d(SDCLKL\_Add)}$	Address valid time	-	1.5	
$t_{d(SDCLKL\_SDNWE)}$	SDNWE valid time	-	1	
$t_{h(SDCLKL\_SDNWE)}$	SDNWE hold time	0	-	
$t_{d(SDCLKL\_SDNE)}$	Chip select valid time	-	0.5	
$t_{h(SDCLKL-\_SDNE)}$	Chip select hold time	0	-	
$t_{d(SDCLKL\_SDNRAS)}$	SDNRAS valid time	-	2	
$t_{h(SDCLKL\_SDNRAS)}$	SDNRAS hold time	0	-	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS valid time	-	0.5	
$t_{d(SDCLKL\_SDNCAS)}$	SDNCAS hold time	0	-	
$t_{d(SDCLKL\_NBL)}$	NBL valid time	-	0.5	
$t_{h(SDCLKL\_NBL)}$	NBLoutput time	0	-	

1. CL = 30 pF on data and address lines. CL=15pF on FMC_SDCLK.
2. Guaranteed by characterization results.

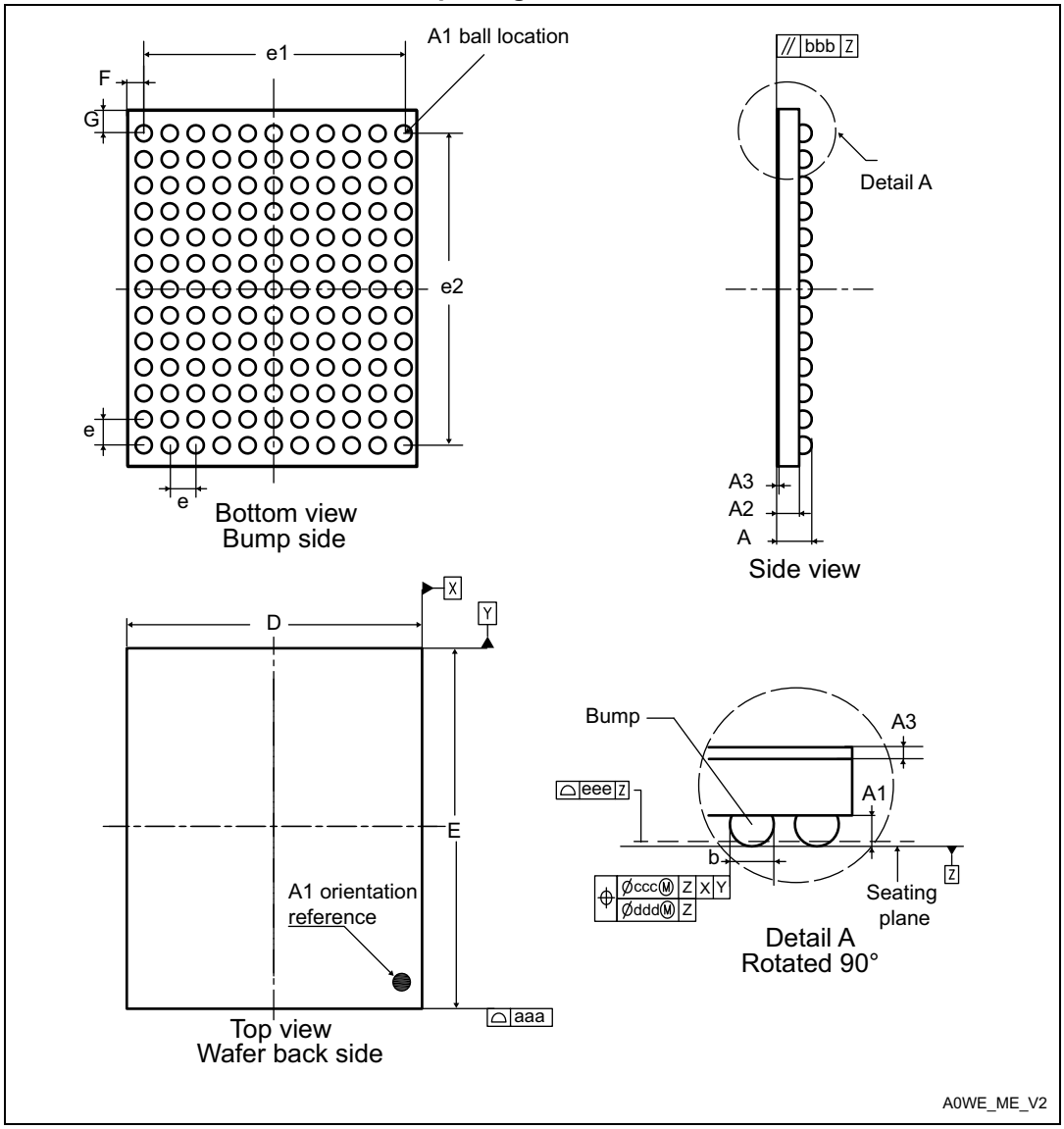
Table 105. LPSDR SDRAM write timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(SDCLK)}$	FMC_SDCLK period	$2T_{HCLK} - 0.5$	$2T_{HCLK}+0.5$	ns
$t_{d(SDCLKL\_Data)}$	Data output valid time	-	5	
$t_{h(SDCLKL\_Data)}$	Data output hold time	2	-	
$t_{d(SDCLKL\_Add)}$	Address valid time	-	2.8	
$t_{d(SDCLKL-SDNWE)}$	SDNWE valid time	-	2	
$t_{h(SDCLKL-SDNWE)}$	SDNWE hold time	1	-	
$t_{d(SDCLKL-\ SDNE)}$	Chip select valid time	-	1.5	
$t_{h(SDCLKL-\ SDNE)}$	Chip select hold time	1	-	
$t_{d(SDCLKL-SDNRAS)}$	SDNRAS valid time	-	1.5	
$t_{h(SDCLKL-SDNRAS)}$	SDNRAS hold time	1.5	-	
$t_{d(SDCLKL-SDNCAS)}$	SDNCAS valid time	-	1.5	
$t_{d(SDCLKL-SDNCAS)}$	SDNCAS hold time	1.5	-	
$t_{d(SDCLKL\_NBL)}$	NBL valid time	-	1.5	
$t_{h(SDCLKL-NBL)}$	NBL output time	1.5	-	

1. CL = 10 pF.
2. Guaranteed by characterization results.

7.2 WLCSP143 package information

Figure 83. WLCSP143 - 143-ball, 4.521x 5.547 mm, 0.4 mm pitch wafer level chip scale package outline



1. Drawing is not to scale.

8 Part numbering

Table 122. Ordering information scheme

Example: STM32 F 429 V I T 6 xxx

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

F = general-purpose

Device subfamily

427= STM32F427xx, USB OTG FS/HS, camera interface, Ethernet

429= STM32F429xx, USB OTG FS/HS, camera interface, Ethernet, LCD-TFT

Pin count

V = 100 pins

Z = 143 and 144 pins

A = 169 pins

I = 176 pins

B = 208 pins

N = 216 pins

Flash memory size

E = 512 Kbytes of Flash memory

G = 1024 Kbytes of Flash memory

I = 2048 Kbytes of Flash memory

Package

T = LQFP

H = BGA

Y = WLCSP

Temperature range

6 = Industrial temperature range, –40 to 85 °C.

7 = Industrial temperature range, –40 to 105 °C.

Options

xxx = programmed parts

TR = tape and reel

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.

9 Revision history

Table 124. Document revision history

Date	Revision	Changes
19-Mar-2013	1	Initial release.
10-Sep-2013	2	Added STM32F429xx part numbers and related informations. **STM32F427xx part numbers:** Replaced FSMC by FMC added Chrom-ART Accelerator and SAI interface. Increased core, timer, GPIOs, SPI maximum frequencies Updated *Figure 8*.Updated *Figure 9*. Removed note in *Section ·: Standby mode*. Updated *Figure 18*. Updated *Table 10: STM32F427xx and STM32F429xx pin and ball definitions* and *Table 12: STM32F427xx and STM32F429xx alternate function mapping*.. Modified *Figure 19: Memory map*. Updated *Table 17: General operating conditions*, *Table 18: Limitations depending on the operating power supply range*. Removed note 1 in *Table 22: reset and power control block characteristics*. Added *Table 23: Over-drive switching characteristics*. Updated *Section : Typical and maximum current consumption*, *Table 34: Switching output I/O current consumption*, *Table 35: Peripheral current consumption* and *Section : On-chip peripheral current consumption*. Updated *Table 36: Low-power mode wakeup timings*. Modified *Section : High-speed external user clock generated from an external source*, *Section : Low-speed external user clock generated from an external source*, and *Section 6.3.10: Internal clock source characteristics*. Updated *Table 43: Main PLL characteristics* and *Table 45: PLLISAI (audio and LCD-TFT PLL) characteristics*. Updated *Table 52: EMI characteristics*. Updated *Table 57: Output voltage characteristics* and *Table 58: I/O AC characteristics*. Updated *Table 60: TIMx characteristics*, *Table 61: I^2C characteristics*, *Table 62: SPI dynamic characteristics*, *Section : SAI characteristics*. Updated *Table 102: SDRAM read timings* and *Table 104: SDRAM write timings*.